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Electronic structure and conduction-band mass of InN under pressure NIELS E. CHRISTENSEN, Dept. of Physics and Astronomy, University of Aarhus, DK-8000 Aarhus, Denmark, IZA GORCZYCA, Inst. of High Pressure Physics, Polish Academy of Scieces, Warsaw, Poland, AXEL SVANE, Dept. of Physics and Astronomy, University of Aarhus, DK-8000 Aarhus C, Denmark — An initio calculations for n-type InN of the band structure and effective masses (opticaland curvature-) in the lowest conduction band as functions of applied pressure and varying electron concentration are presented. The calculations as well as available experimental data demonstrate the strong non-parabolicity of the InN conduction band.

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